Onsemi

PNP Silicon General Purpose High Voltage Transistor

MSB92T1G

This PNP Silicon Planar Transistor is designed for general purpose amplifier applications. This device is housed in the SC-59 package which is designed for low power surface mount applications.

Features

• This is a Pb–Free Device

MAXIMUM RATINGS (T_A = 25°C)

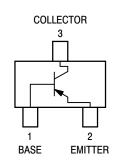
Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	-300	Vdc
Collector-Emitter Voltage	V _{(BR)CEO}	-300	Vdc
Emitter-Base Voltage	V _{(BR)EBO}	-5.0	Vdc
Collector Current – Continuous	Ι _C	150	mAdc

THERMAL CHARACTERISTICS

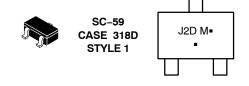
Rating	Symbol	Max	Unit
Power Dissipation (Note 1)	PD	150	mW
Junction Temperature	Т _Ј	150	°C
Storage Temperature Range	T _{stg}	-55~+150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.







J2D = Device Marking Code M = Date Code . = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MSB92T1G	SC–59 (Pb–Free)	3000/Tape & Reel

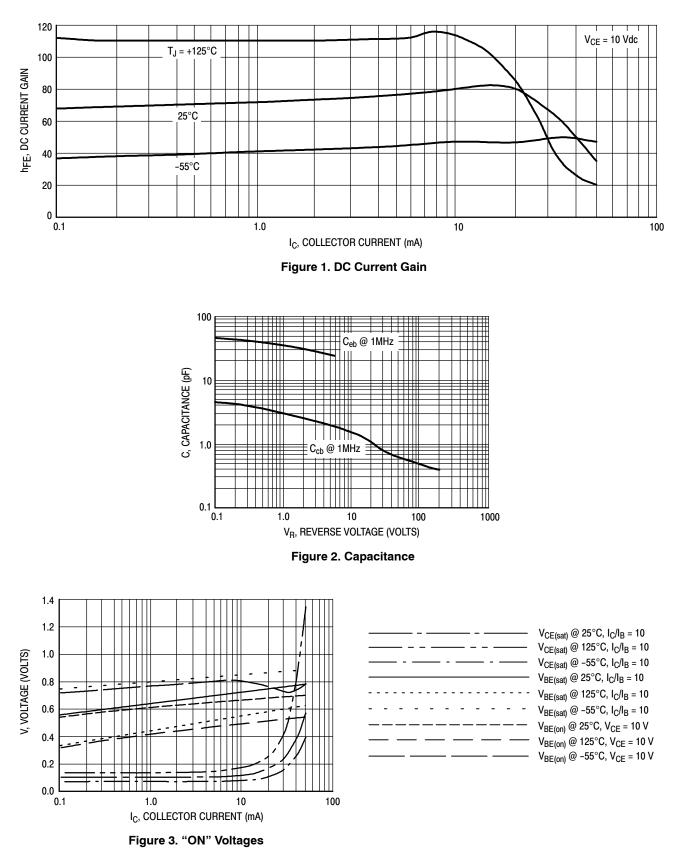
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage $(I_{C} = -1.0 \text{ mAdc}, I_{B} = 0)$	V _{(BR)CEO}	-300	-	Vdc
Collector-Base Breakdown Voltage $(I_C = -100 \ \mu Adc, I_E = 0)$	V _{(BR)CBO}	-300	-	Vdc
Emitter-Base Breakdown Voltage $(I_E = -100 \ \mu Adc, I_E = 0)$	V _{(BR)EBO}	-5.0	-	Vdc
Collector-Base Cutoff Current ($V_{CB} = -200 \text{ Vdc}, I_E = 0$)	I _{CBO}	-	-0.25	μΑ
Emitter–Base Cutoff Current ($V_{EB} = -3.0 \text{ Vdc}, I_B = 0$)	I _{EBO}	_	-0.1	μΑ
$ \begin{array}{l} \text{DC Current Gain (Note 2)} \\ (V_{\text{CE}} = -10 \ \text{Vdc}, \ \text{I}_{\text{C}} = -1.0 \ \text{mAdc}) \\ (V_{\text{CE}} = -10 \ \text{Vdc}, \ \text{I}_{\text{C}} = -10 \ \text{mAdc}) \\ (V_{\text{CE}} = -10 \ \text{Vdc}, \ \text{I}_{\text{C}} = -30 \ \text{mAdc}) \end{array} $	h _{FE1} h _{FE2} h _{FE3}	25 40 25		-
Collector-Emitter Saturation Voltage $(I_C = -20 \text{ mAdc}, I_B = -2.0 \text{ mAdc})$	V _{CE(sat)}	_	-0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = -20$ mAdc, $I_B = -2.0$ mAdc)	V _{BE(sat)}	-	-0.9	Vdc
SMALL SIGNAL CHARACTERISTICS				
Current-Gain – Bandwidth Product (I _C = -10 mAdc, V _{CE} = -20 Vdc, f = 20 MHz)	fT	50	_	MHz
Collector-Base Capacitance $(V_{CB} = -20 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{cb}	-	6.0	pF

2. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2%.

MSB92T1G



semi



SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318**

ISSUE AU

DATE 14 AUG 2024













XXX = Specific Device Code М = Date Code

= Pb-Free Package .

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



MILLIMETERS					
DIM	MIN	NOM	МАХ		
А	0.89	1.00	1.11		
A1	0.01	0.06	0.10		
b	0.37	0.44	0.50		
с	0.08	0.14	0.20		
D	2.80	2.90	3.04		
E	1.20	1.30	1.40		
е	1.78	1.90	2.04		
L	0.30	0.43	0.55		
L1	0.35	0.54	0.69		
Ηe	2.10	2.40	2.64		
Т	0°		10°		

NOTES:

DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS: 1.

2. MILLIMETERS.

MILLIME IERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE 3.

BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, 4. PROTRUSIONS, OR GATE BURRS.

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	I	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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